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(54) METHOD FOR MANUFACTURING NITRIDE SEMICONDUCTOR LIGHT-EMITTING ELEMENT

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(57) **ABSTRACT**

Manufacturing a nitride semiconductor light-emitting device includes a depositing an n-type cladding layer and an active layer with a multi-quantum well structure having a plurality of well layers on a substrate in a chamber. In depositing the active layer, a silicon source is not supplied into the chamber. The method includes supplying the silicon source into the chamber after depositing the n-type cladding layer and before depositing the active layer thereby, when a well layer located second from the n-type cladding layer side among the plurality of well layers is defined as a second well layer, a peak of distribution of a silicon concentration in a stacking direction of the n-type cladding layer and the active layer appears in a range where the second well layer is formed, and the silicon concentration at an apex of the peak is not less than 1.49×10^{18} atoms/cm^3 and not more than 4.96×10^{18} atoms/cm^3.